

Silicon PNP Power Transistors

2SA1633

DESCRIPTION

- With TO-247 package
- Complement to type 2SC4278
- High current and high power capability

APPLICATIONS

- For audio output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

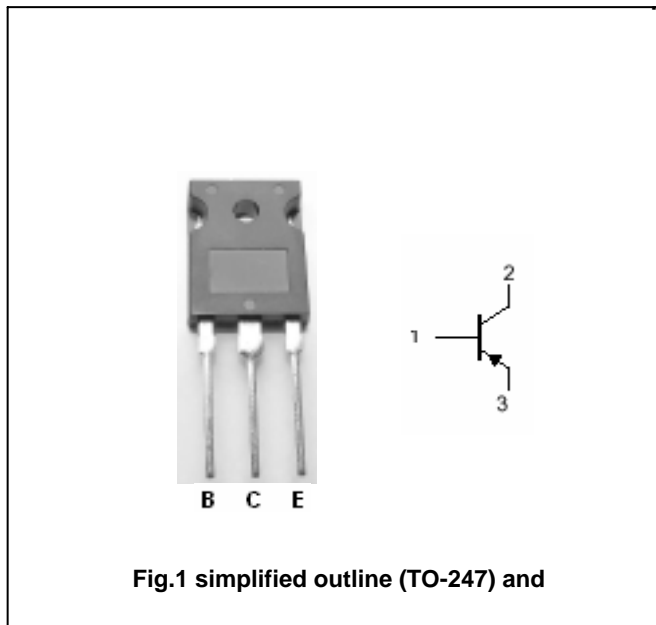


Fig.1 simplified outline (TO-247) and

Absolute maximum ratings(Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-150	V
V _{CEO}	Collector-emitter voltage	Open base	-150	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-10	A
P _D	Total power dissipation	T _C =25	100	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA; I _B =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A ; I _B =-0.5A			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-5A ; I _B =-0.5A			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-5V	60		320	
f _T	Transition frequency	I _C =-1A ; V _{CE} =-10V		20		MHz

◆ h_{FE} Classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

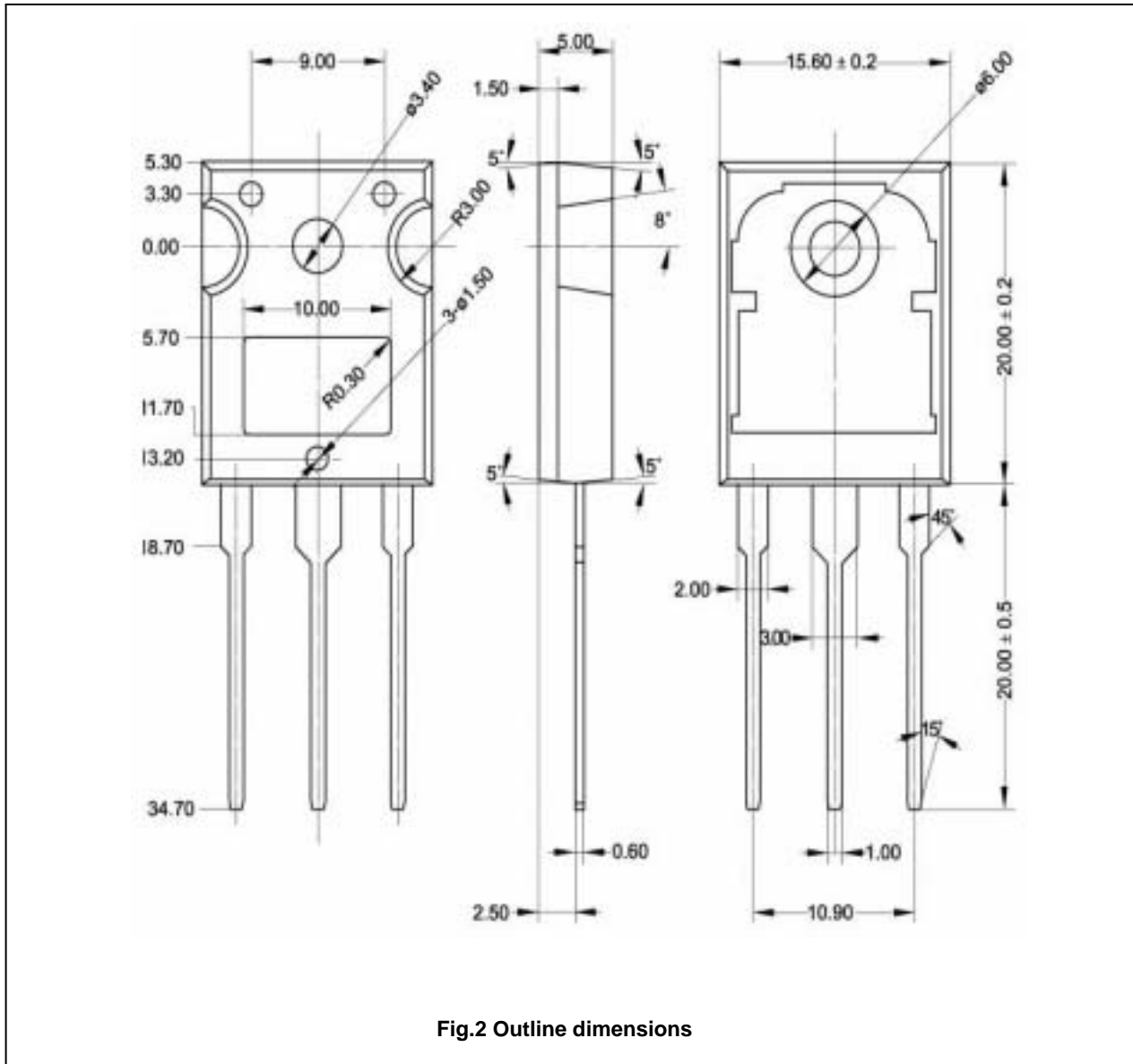


Fig.2 Outline dimensions